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(19) **United States**(12) **Patent Application Publication** (10) **Pub. No.: US 2007/0191243 A1**
Moore (43) **Pub. Date: Aug. 16, 2007**(54) **REMOVAL OF SILICA BASED ETCH
RESIDUE USING AQUEOUS CHEMISTRY**(52) **U.S. Cl. 510/175**(75) **Inventor: John C. Moore, Camarillo, CA (US)**(57) **ABSTRACT**

Correspondence Address:

**ARTHUR J. PLANTAMURA
GENERAL CHEMICAL PERFORMANCE
PRODUCTS LLC.
90 EAST HALSEY ROAD
PARSIPPANY, NJ 07054 (US)**(73) **Assignee: GENERAL CHEMICAL PERFOR-
MANCE PRODUCTS, LLC, Parsip-
pany, NJ (US)**(21) **Appl. No.: 11/307,556**(22) **Filed: Feb. 13, 2006****Publication Classification**(51) **Int. Cl.
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Removal of silica-based etch residue is effected by use of an aqueous chemistry which eliminates hazard concerns in connection with electronic component fabrication tooling. The system employs a formulated product comprising a controlled level of ionized fluorine in a citrate buffer containing a dual surfactant system for etch residue penetration and rinsing. The combined system is proven to be ideal for Si-based etch residue dissolution and removal. The Si-residue removal rates have been characterized at specific buffered pH values and normal process conditions at times between 45 sec. to 3 min., and with those described being effectual at times of the order of 45 sec. or less when processed in a single-wafer tool. The product simplifies and reduces cost time and materials.

